Silicon NPN Power Transistors 2SD898

DESCRIPTION

- With TO-3 package
- Built-in damper diode
- High voltage ,high power dissipation
- Wide area of safe operation

APPLICATIONS

- For TV horizontal deflection output applications

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

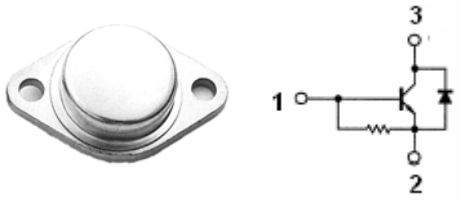


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	1500	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		3	A
I_{CM}	Collector current-peak		3.5	A
P_T	Total power dissipation	T_C=25℃	50	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

Silicon NPN Power Transistors 2SD898

CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=200mA; I_C=0;	6			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=2.5A;I_B=0.8 A			5.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C=2.5A;I_B=0.8 A			1.5	V
I_{CES}	Collector cut-off current	V_{CE}=1500V;R_{BE}=0			0.5	mA
I_{EBO}	Emitter cut-off current	V_{EB}=6V;I_C=0	50		200	mA
h_{FE}	DC current gain	I_C=0.5A ; V_{CE}=5V	10		40	
V_F	Diode forward voltage	I_F=3A			2.2	V

PACKAGE OUTLINE

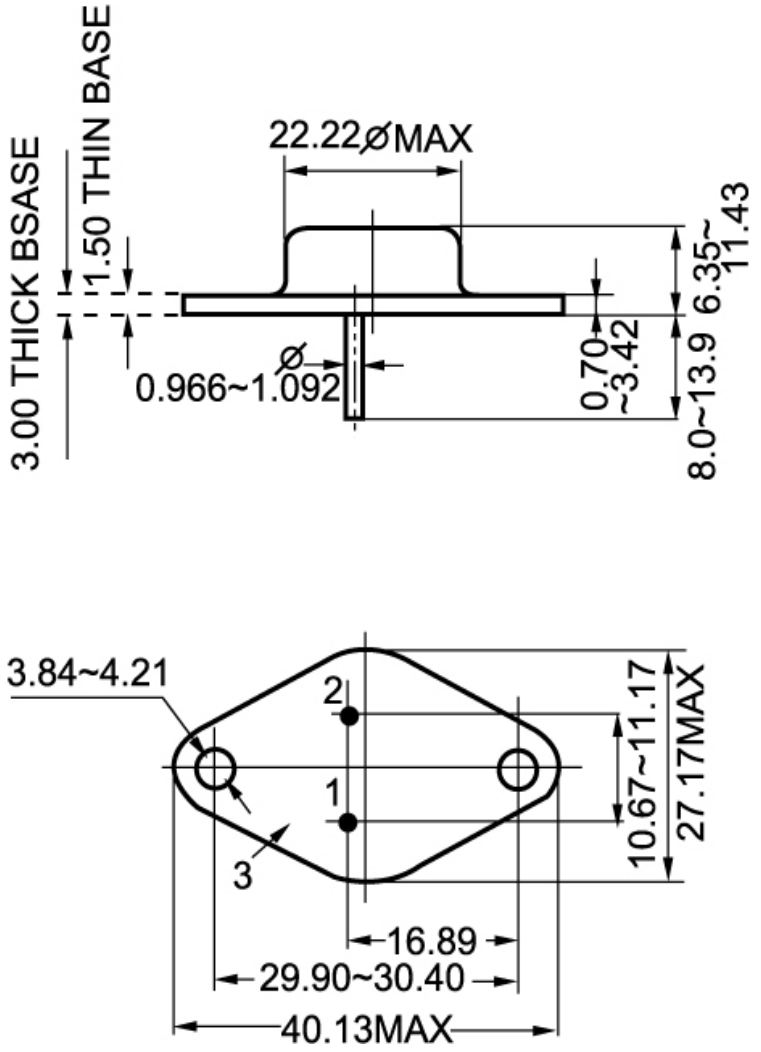


Fig.2 Outline dimensions